## 8K×8 Bit Mask ROM

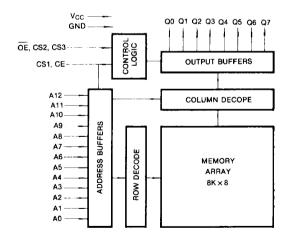
#### **FEATURES**

- 2364/65: Non-power down
- 2364S/65S: Automatic power down
- · Fully static operation
- Silicon gate NMOS technology
- Maximum access time 2364/65-20: 200 ns 2364/65-25: 250 ns 2364/65-30: 300 ns
- Programmable chip selects
- 3-State outputs
- Fully TTL compatible
- Single ±10% 5 volt supply
- Pin compatible with 2564 EPROM's
- Available in 3 temperature ranges 2364/65 (Commercial): 0°C to 70°C 2364I/65I (Industrial): -40°C to 85°C 2364HR/65HR (Military): -55°C to 125°C

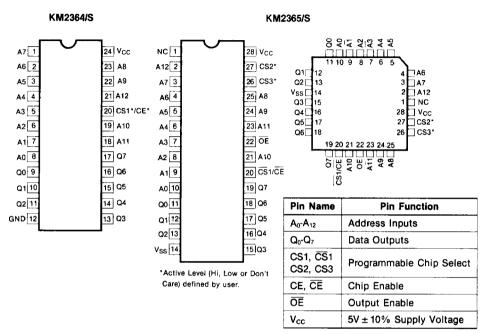
#### GENERAL DESCRIPTION

The KM2365/65 are mask programmable read only memories with 8K word by 8 bit organizations. Designed for ease of use, these devices require only a 5-volt supply, are TTL compatible, and because of their totally static (asynchronous) operation require no clock. These memory devices are available in two versions. The 2364/65 are non-power down versions where the active level of chip selects CS1 (on the 2364), and CS2 and CS3 (on the 2365) are programmable and defined by the user to facilitate system memory expansion. The 2364S and 2365S are standby versions offering an automatic powerdown feature controlled by the chip enable CE input. When CE goes high, the device automatically powers down and remains in a low power standby mode as long as CE remains high. Also to provide easier system implementation, the active level of chip enable CE (on the 2364S), and chip selects CS2 and CS3 (on the 2365S) is programmable. The KM2364 is packaged in a 24 pin DIP, and the 2365 is packaged in a 28 pin DIP, both with industry standard byte-wide JEDEC pin-outs. Optionally, the 2365 is available in a space saving 28 pin surface mounted plastic leaded chip carrier.

### **FUNCTIONAL BLOCK DIAGRAM**



#### PIN CONFIGURATION



# ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Characteristic	Symbol	Value	Unit
Voltage on Any Pin with Respect to Ground Storage Temperature	V <sub>CC</sub> T <sub>stg</sub>	-0.5 to +7V -65 to +150	°C

Stresses above "absolute maximum ratings" may result in damage to the device. Functional operation of devices at the "absolute maximum ratings" or above the recommended operating conditions stipulated elsewhere in this specification is not implied.

#### RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	KM2364/65		KM2364I/65I			KM2364HR/65HR			11-14-	
		Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Units
Supply Voltage*	V <sub>CC</sub>	4.5	5.0	5.5	4.5	5.0	5.5	4.5	5.0	5.5	Volts
Input High Level Voltage	V <sub>IH</sub>	2.0		Vcc	2.0		V <sub>cc</sub>	2.2		Vcc	Volts
Input Low Level Voltage	V <sub>1L</sub>	- 0.5		0.8	- 0.5		0.8	- 0.5		0.8	Volts
Operating Ambient Temperature	TA	0		70	- 40		85	- 55		125	°C

 $<sup>^*</sup>V_{CC}$  must be applied at least  $100\mu s$  before proper device operation is achieved.



# STATIC ELECTRICAL CHARACTERISTICS OVER RECOMMENDED OPERATING CONDITIONS (UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Тур	Max	Units
Input Leakage Current	I <sub>IN</sub>	V <sub>IN</sub> = 0V to V <sub>CC</sub> max			10	μΑ
Output Leakage Current	lo	V <sub>o</sub> = 0.2 to V <sub>cc</sub> max Chip Deselected			± 10	μΑ
Output High Voltage	V <sub>OH</sub>	$I_{OH} = -200\mu A$	2.4			Voits
Output Low Voltage	Vol	I <sub>OL</sub> = 3.2mA			0.4	Volts
Supply Current-Active	Icc	Outputs Open			60	mA
Supply Current-Standby	I <sub>SB</sub> *	Chip Deselected			10	μΑ

<sup>\*</sup>Applies to KM2364S/65S Power Down Versions only.

### CAPACITANCE (Ta = 25°C, f = 1 MHz)

Parameter	Symbol	Test Condition	Min	Тур	Max	Units
Input Capacitance	C <sub>IN</sub>	All pins except pin under test			7	pF
Output Capacitance	Co	are tied to ground			12.5	pF

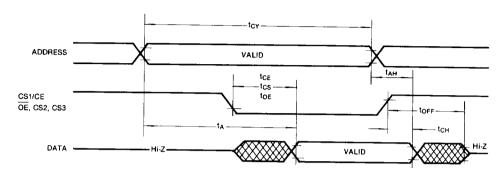
Notes: Characteristics are the same for all Operating Temperature Ranges.

# **AC CHARACTERISTICS**

# AC CHARACTERISTICS OVER RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	2364/65-20, 2364l/65l-20, 2364HR/65HR-20		2364/65-25, 2364V65I-25, 2364HR/65HR-25		2364/65-30, 2364I/65I-35, 2364HR/65HR-30		Units
		Min	Max	Min	Max	Min	Max	
Cycle Time	t <sub>CY</sub>	200			250		300	ns
Address Access Time	t <sub>A</sub>	1	300	200		250		ns
Chip Enable Access Time	t <sub>CE</sub>	200			250		300	ns
Chip Select Access Time	t <sub>CS</sub>	1	150	100		120		ns
Chip Select to Data Off (Hi Z)	toff		150	100		120		ns
Data Hold Time from Control	t <sub>CH</sub>	0			0		0	ns
Data Hold Time from Address	t <sub>AH</sub>	0	1	†		0	_	ns

# TIMING DIAGRAMS AC WAVEFORMS

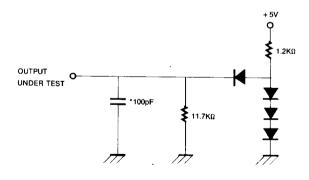


The chip select line is assumed to be active low.

### **AC CONDITION OF TESTS**

Input Pulse Levels	0.8 Volts to 2.0 Volts
Input Rise & Fall Times	10 ne
Output Timing Levels	0.8 Volts to 2.0 Volts

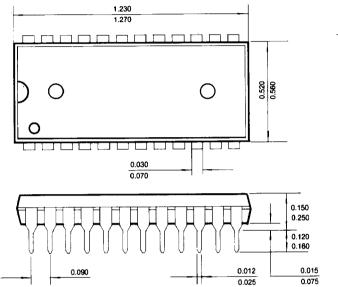
# **AC TEST LOAD CIRCUIT**

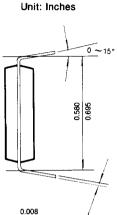


\*includes jig capacitance.
All diodes 1N3064 or equivalent.

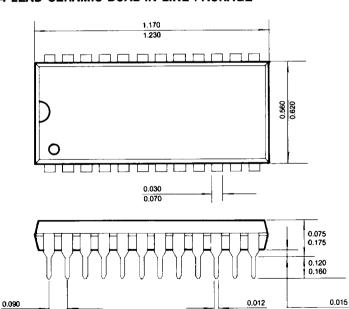
# PACKAGE DIMENSIONS (Continued)

#### 24 LEAD PLASTIC DUAL IN LINE PACKAGE



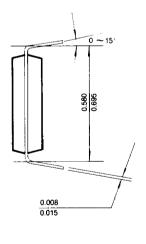


# 24 LEAD CERAMIC DUAL IN LINE PACKAGE



#### Unit: Inches

0.015



0.075

0.025

0.110

Unit: Inches

# PACKAGE DIMENSIONS 28 LEAD PLASTIC DUAL IN LINE PACKAGE

1.430 1.480 0.520 0.030 0.070 0.008 0.015 0.150 0.250 0.120 0.160 0.090 0.012 0.015 0.110 0.025 0.074

# 28 LEAD CERAMIC DUAL IN LINE PACKAGE

